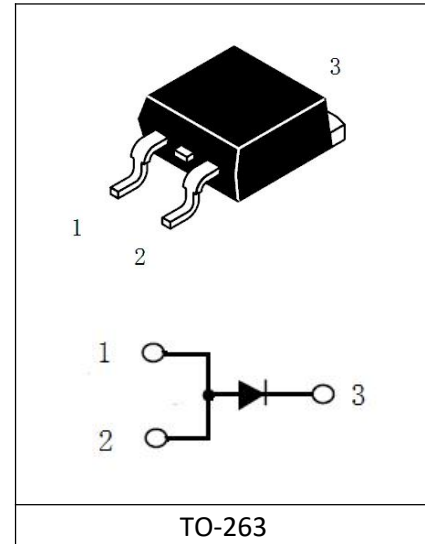


SCHOTTKY RECTIFIERS

Features:

- Low power loss,high efficiency
- High surge capacity
- High ESD capacity : HBM,3B (>8000V)
- For use in low voltage,high frequency inverters, free wheeling,and polarity protection applications
- Metal silicon junction,majority carrier conduction
- Guard ring for over voltage protection



Absolute Maximum Ratings(Tc=25°C):

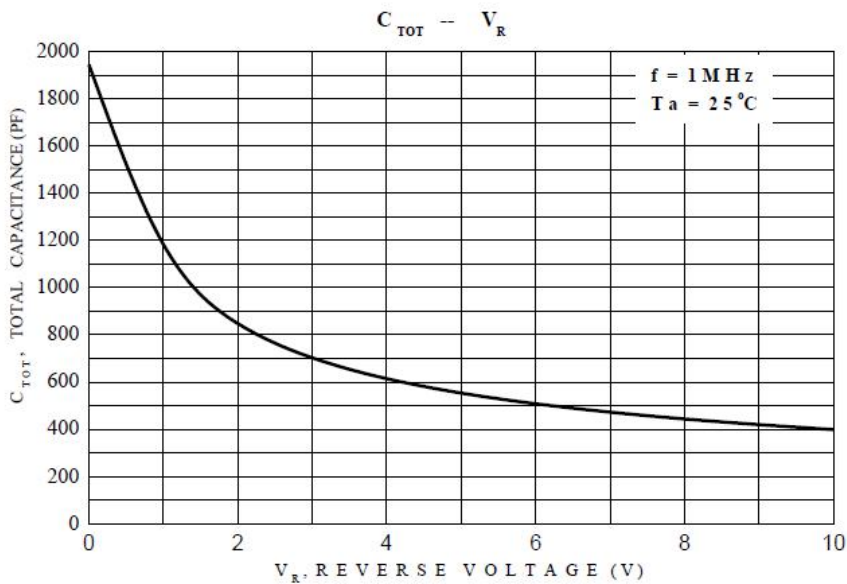
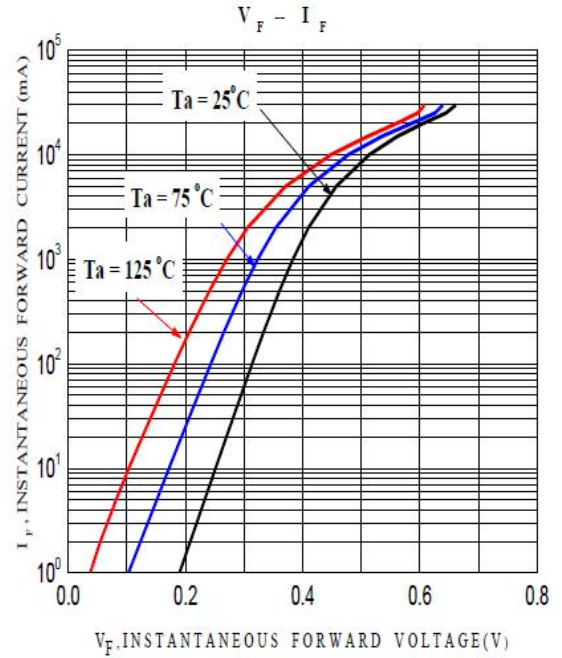
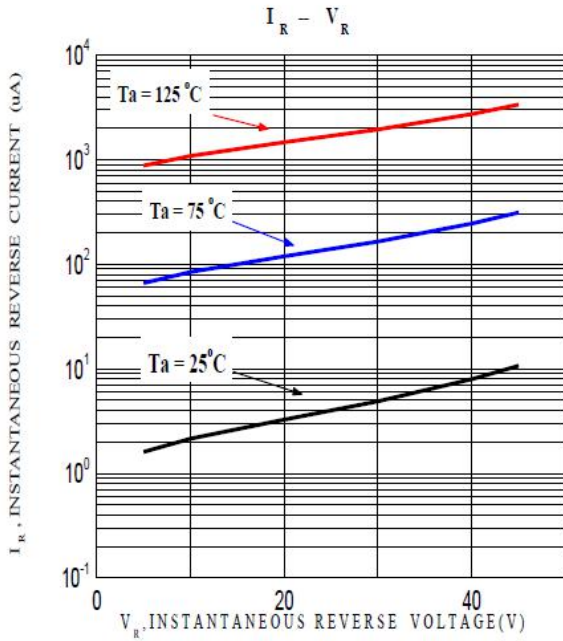
Characteristics	Symbol	Rating	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	45	V
Average Rectified Forward Current	$I_{F(AV)}$	15	A
Non-repetitive Peak Forward Surge Current 8.3ms Single Half-Sine-Wave	I_{FSM}	350	A
Collector power dissipation	P_{tot}	2.5	W
Junction temperature	T_j	175	°C
Storage temperature range	T_{STG}	-55~175	°C

Electrical Characteristics(Tc=25°C) :

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=15A; T_C=25^\circ C$		0.52	0.60	V
Reverse Current	I_R	$V_R=45V; T_C=25^\circ C$ $V_R=45V; T_C=125^\circ C$		0.02	0.12 15.0	mA
Peak Repetitive Reverse Surge Current	I_{RRM}	2.0 us Pulsu Width ,f=1.0KHZ $T_J<175^\circ C$			1.0	A

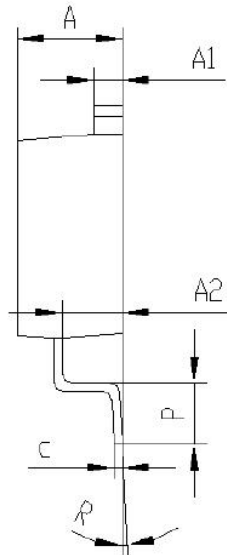
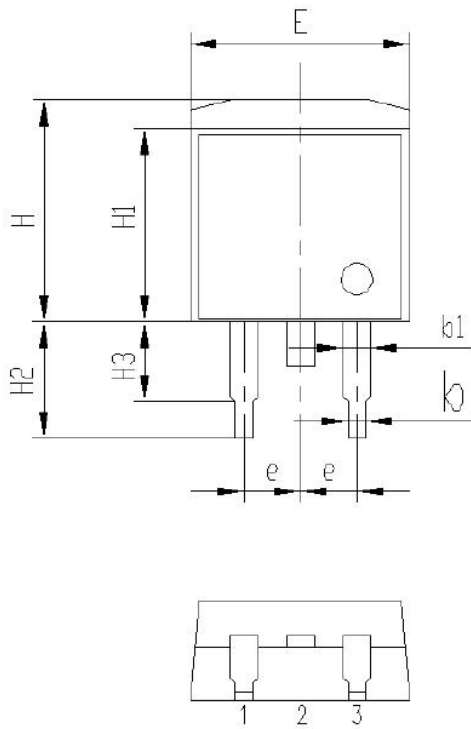
Symbol	Paramter	Typ	Units
$R_{\theta JA}$	Junction-to-Ambient	50	°C/W

TYPICAL CHARACTERISTICS



Package Information

TO-263 PACKAGE



	単位: mm		
	MIN	NOM	MAX
A	4.5	4.7	4.9
A1	1.17	1.27	1.37
A2	2.4	2.6	2.8
b	0.6	0.8	1.0
b1	0.95	1.15	1.35
c	0.26	0.38	0.5
e	2.34	2.54	2.74
E	9.7	9.9	10.1
H	9.8	10	10.2
H1	8.5	8.7	8.9
H2	5.05	5.25	5.45
H3	3.6	3.8	4
R	0	3°	6°
P	2.55	2.75	2.95